

ABSTRACT

The present invention provides a method of fabricating a portion of a memory cell, the method comprising providing a first conductor in a trench which is provided in an insulating layer and flattening an upper surface of the insulating layer and the first conductor, forming a material layer over the flattened upper surface of the insulating layer and the first conductor and flattening an upper portion of the material layer while leaving intact a lower portion of the material layer over the insulating layer and the first conductor.